

IN THE CLAIMS:

~~Please add the following new claims 10 through 16:~~

-- Claim 10. A method of CMP comprising:

forming a CMP slurry containing cerium oxide;

adding a slurry modifier to the slurry to produce a modified slurry that polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure having high structure areas and low structure areas using the modified slurry, whereby high structure areas are polished at a rate approximating a blanket polishing rate and low structure areas are polished at a substantially zero rate.

Claim 11. The method of claim 10, wherein the high structure areas and the low structure areas are both formed of silicon dioxide.

Claim 12. The method of claim 10, wherein the slurry modifier is ethylene glycol.

Claim 13. A method of CMP comprising:

forming a CMP slurry having a high structure polishing rate lower than a blanket polishing rate;

adding a slurry modifier to the slurry to produce a modified slurry that polishes high structures at a rate approximating the blank polishing rate; and

polishing high structure areas.